

Christophe A Hurni

List of Publications by Year in descending order

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9
papers

517
citations

1162889

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h-index

1474057

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g-index

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docs citations

9
times ranked

752
citing authors

#	ARTICLE	IF	CITATIONS
1	Quantum Efficiency of III-Nitride Emitters: Evidence for Defect-Assisted Nonradiative Recombination and its Effect on the Green Gap. <i>Physical Review Applied</i> , 2019, 11, .	1.5	66
2	Electrical properties of III-Nitride LEDs: Recombination-based injection model and theoretical limits to electrical efficiency and electroluminescent cooling. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	46
3	Design, fabrication, and performance analysis of GaN vertical electron transistors with a buried p/n junction. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	81
4	Bulk GaN flip-chip violet light-emitting diodes with optimized efficiency for high-power operation. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	197
5	High light extraction efficiency in bulk-GaN based volumetric violet light-emitting diodes. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	37
6	m-plane (101 $\bar{1}$) and (202 $\bar{1}$) GaN/Al _x Ga _{1-x} N conduction band offsets measured by capacitance-voltage profiling. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	6
7	Effects of growth temperature on Mg-doped GaN grown by ammonia molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012, 101, .	1.5	29
8	Capacitance-voltage profiling on polar III-nitride heterostructures. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	10
9	p-n junctions on Ga-face GaN grown by NH ₃ molecular beam epitaxy with low ideality factors and low reverse currents. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	45